

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Grutzediek et al. Confirmation No.: 4906  
Serial No.: 09/806,224 Examiner: George Fourson  
Filed: 06/11/2001 Group Art Unit: 2823  
Title: Method for Producing Transistors

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

RESPONSE

Dear Sir:

In response to the Office Action dated March 1, 2006, Applicant is submitting this Request for Reconsideration and the accompanying Declaration Under 35 U.S.C. 132.

The three-month period for responding to the last Office Action expired on June 1, 2006. A Request for a three-month extension of time and the associated fee are enclosed herewith. Accordingly, this Response is timely filed.

In the last Office Action, pending claims 1-27 and 29-31 were rejected under 35 U.S.C. 103(a) as allegedly unpatentable over Sakurai et al. (EP 0 032 022) alone or in combination with Nemoto (JP 9027551). This rejection is respectfully, but most strenuously traversed.

Applicants' attorney had scheduled a personal interview to discuss this rejection with the Examiner at the United States Patent and Trademark Office for August 8, 2006. Unfortunately, the Examiner was not available when Applicants' attorney arrived for this interview.

The prior art rejection relies on the Sakurai et al. reference for teaching a method of forming integrated circuit devices which allegedly employs energy that assures a weakly doped inner area remains on a surface of a weakly doped semiconductor substrate when an oppositely doped trough is formed in the substrate by ion implantation. The parameters of this method are not disclosed in the relevant portion (pages 2-3 and Figures 2-6) of the applied reference. However, the reference explicitly teaches that this method is proposed in Japanese Patent Application No. 50-364.

An English translation of this Japanese patent application was earlier obtained and provided to the Examiner. Applicants respectfully submit that the method and parameters disclosed in the Japanese patent application would not produce and therefore is not an enabling disclosure of the method defined by pending independent claim 1.

In support of these assertions, Applicant previously submitted a document detailing the Difference between the Fujitsu-Patent and the Invention (another copy enclosed for the Examiner's convenience). This document explains why ion energies for the implantation of a N-trench must be well above 1MeV to produce high quality semiconductor devices. The document also provides evidence that the method and parameters of the applied reference would not achieve the same results as the claimed invention.

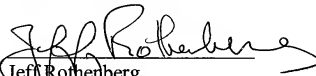
In further support of these assertions, Applicant is submitting herewith a Declaration Under 35 U.S.C. 132. This Declaration contains further factual support for the conclusion that the applied primary reference, including the incorporated Japanese patent document, does not constitute an enabling disclosure of the method of currently pending independent claim 1.

The secondary reference to Nemoto adds nothing that would overcome the fundamental deficiency of the primary reference.

For all of the above reasons, the Examiner is respectfully requested to reconsider and withdraw the sole remaining grounds for rejection. Allowance of all of the pending claims is respectfully requested.

If it would advance the prosecution of this application, the Examiner is cordially invited to contact Applicant's representative at the below indicated telephone number.

Respectfully submitted,

  
Jeff Rothenberg  
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Dated: August 30, 2006

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